

PASSIVATION FOR IMPROVED BIPOLAR YIELD

ABSTRACT OF THE DISCLOSURE

- 5 A SiGe heterojunction bipolar transistor including at least an emitter formed on a SiGe base region wherein the sidewalls of the emitter are protected by a conformal passivation layer. The conformal passivation layer is formed on the exposed sidewalls of said emitter prior to siliciding the structure. The presence of the passivation layer in the structure prevents silicide shorts from occurring by eliminating bridging
- 10 between adjacent silicide regions; therefore improved SiGe bipolar yield is obtained. A method for forming such a structure is also provided.

FOR OFFICIAL USE ONLY